



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

48 A

Features

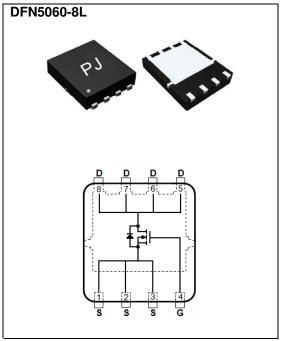
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_{D}@20A<17m\Omega$
- R_{DS(ON)}, V_{GS}@4.5V, I_D@10A<20mΩ
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20		
Continuous Drain Current (Note 4)	T _C =25°C	l _D	48	А	
	T _C =100°C		30		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	192		
Power Dissipation	T _C =25°C	PD	100	W	
	T _C =100°C		50		
Continuous Drain Current (Note 4)	T _A =25°C	Ι _D	7.4	_	
	T _A =70°C		6.0	Α	
Power Dissipation	T _A =25°C	Б.	2.4	W	
	T _A =70°C	Pb	1.6		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	45	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~175	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	1.5	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_D =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1	1.7	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =10V, I_D =20A	-	13	17	mΩ
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =4.5V, I_{D} =10A	-	15	20	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =60V, V_{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	V _{DS} =30V, I _D =10A, V _{GS} =4.5V ^(Note 2,3)	-	13.5	-	nC
Gate-Source Charge	Q_gs		-	4.8	-	
Gate-Drain Charge	Q_{gd}	V _{GS} =4.5 V	-	4.9	-	
Input Capacitance	Ciss	\/ OF\/ \/ O\/	-	1574	-	pF
Output Capacitance	Coss	$V_{DS}=25V, V_{GS}=0V,$	-	118	-	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	77	-	
Turn-On Delay Time	td _(on)	\/ 45\/ L 4A	-	11	-	
Turn-On Rise Time	t _r	V_{DD} =15V, I_{D} =1A, V_{GS} =10V, R_{G} =6 Ω (Note 2,3)	-	11	-	
Turn-Off Delay Time	td _(off)		-	35	-	
Turn-Off Fall Time	t _f		-	8.1	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					10	^
Diode Forward Current	I _S		_		48	Α
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.68	1	V

- Pulse width < 300us, Duty cycle < 2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =30A, V_{DD} =25V, V_{GS} =10V, Starting T_J =25°C
- Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

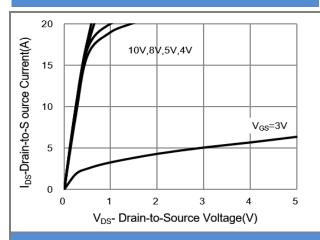


Fig.1 Output Characteristics

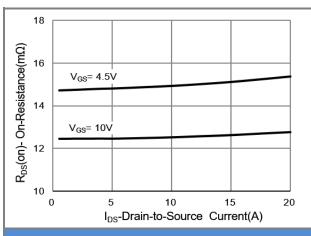
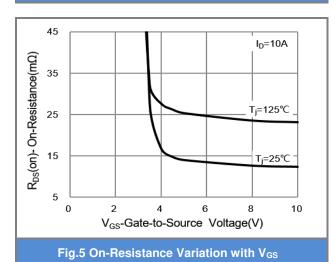


Fig.3 On-Resistance vs. Drain Current



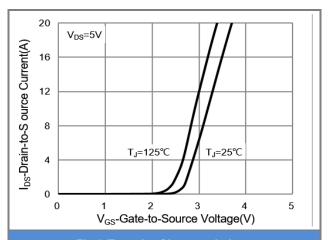


Fig.2 Transfer Characteristics

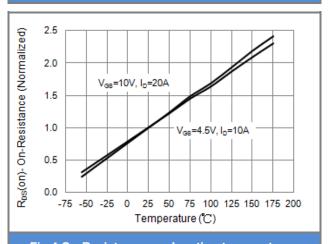


Fig.4 On-Resistance vs. Junction temperature

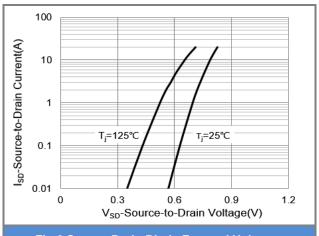


Fig.6 Source-Drain Diode Forward Voltage





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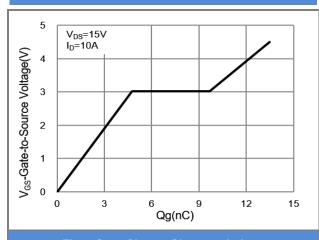


Fig.7 Gate-Charge Characteristics

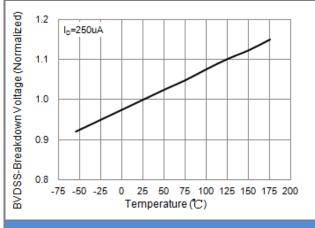


Fig.8 Breakdown Voltage Variation vs. Temperature

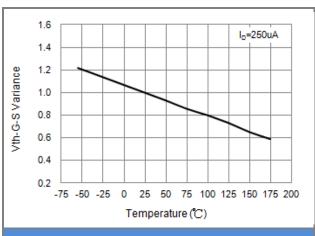


Fig.9 Threshold Voltage Variation with Temperature

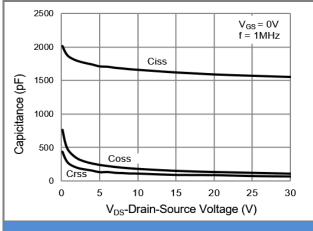
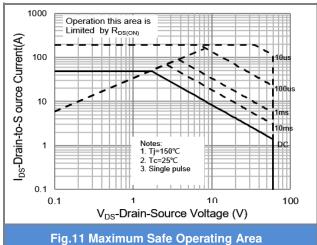


Fig.10 Capacitance vs. Drain-Source Voltage



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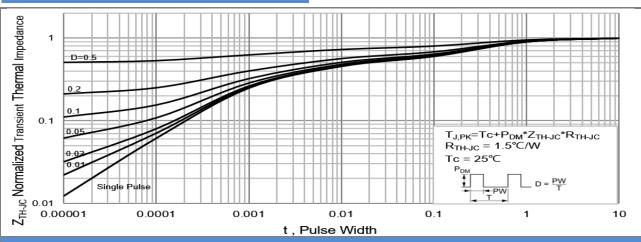


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

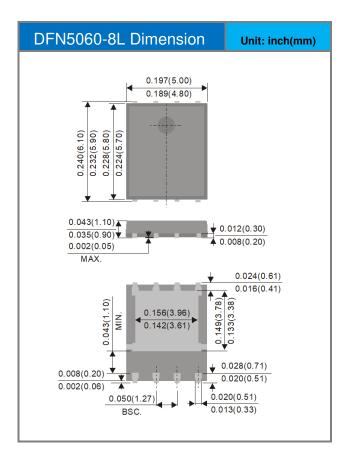


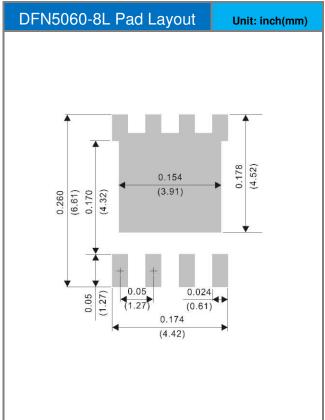


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5466A1-AU_R2_000A1	DFN5060-8L	3000pcs / 13" reel	Q5466A1	Halogen free	

Packaging Information & Mounting Pad Layout









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